Olivier Thomas

List of Publications by Year
in descending order

240 papers	3,773 citations	126907 33 h-index	197818 49 g-index
243 all docs	243 docs citations	243 times ranked	2842 citing authors

#	Article	IF	Citations
1	Crystallographic Anisotropy Dependence of Interfacial Sliding Phenomenon in a Cu(16)/Nb(16) ARB (Accumulated Rolling Bonding) Nanolaminate. Nanomaterials, 2022, 12, 308.	4.1	3
2	Time-resolved piezoelectric response in relaxor ferroelectric (Pb_{0.88}La_{0.12})(Zr_{0.52}Ti_{0.48})O₃ thin films. Journal of Applied Physics, 2022, 131, 064102.	2.5	1
3	X-ray Diffraction Imaging of Deformations in Thin Films and Nano-Objects. Nanomaterials, 2022, 12, 1363.	4.1	3
4	Bragg coherent diffraction imaging of single 20â€…nm Pt particles at the ID01-EBS beamline of ESRF. Journal of Applied Crystallography, 2022, 55, 621-625.	4.5	5
5	Imaging the facet surface strain state of supported multi-faceted Pt nanoparticles during reaction. Nature Communications, 2022, 13, .	12.8	11
6	Inâ€‰situ force measurement during nanoâ€‰indentation combined with Laue microdiffraction. Nano Select, 2021, 2, 99-106.	3.7	2
7	Energy-dispersive X-ray micro Laue diffraction on a bent gold nanowire. Journal of Applied Crystallography, 2021, 54, 80-86.	4.5	5
8	Simultaneous Multi-Bragg Peak Coherent X-ray Diffraction Imaging. Crystals, 2021, 11, 312.	2.2	6
9	Facetâ€Đependent Strain Determination in Electrochemically Synthetized Platinum Model Catalytic Nanoparticles. Small, 2021, 17, e2007702.	10.0	4
10	Crystallization behavior of N -doped Ge-rich GST thin films and nanostructures: An in-situ synchrotron X-ray diffraction study. Microelectronic Engineering, 2021, 244-246, 111573.	2.4	8
11	Berkovich nanoindentation study of 16Ânm Cu/Nb ARB nanolaminate: Effect of anisotropy on the surface pileup. MRS Advances, 2021, 6, 495-499.	0.9	3
12	When More Is Less: Plastic Weakening of Single Crystalline Ag Nanoparticles by the Polycrystalline Au Shell. ACS Nano, 2021, 15, 14061-14070.	14.6	5
13	Twin boundary migration in an individual platinum nanocrystal during catalytic CO oxidation. Nature Communications, 2021, 12, 5385.	12.8	14
14	Ferroelectric nanodomains in epitaxial GeTe thin films. Physical Review Materials, 2021, 5, .	2.4	8
15	Direct Observations of the Structural Properties of Semiconducting Polymer: Fullerene Blends under Tensile Stretching. Materials, 2020, 13, 3092.	2.9	1
16	Mapping Inversion Domain Boundaries along Single GaN Wires with Bragg Coherent X-ray Imaging. ACS Nano, 2020, 14, 10305-10312.	14.6	8
17	First stages of plasticity in three-point bent Au nanowires detected by in situ Laue microdiffraction. Applied Physics Letters, 2020, 116, 243101.	3.3	1
18	Continuous scanning for Bragg coherent X-ray imaging. Scientific Reports, 2020, 10, 12760.	3.3	6

#	Article	IF	Citations
19	Piezoelectric Properties of Pb1â^'xLax(Zr0.52Ti0.48)1â^'x/4O3 Thin Films Studied by In Situ X-ray Diffraction. Materials, 2020, 13, 3338.	2.9	3
20	Stress Buildup Upon Crystallization of GeTe Thin Films: Curvature Measurements and Modelling. Nanomaterials, 2020, 10, 1247.	4.1	2
21	In situ measurements of the structure and strain of a Ï€-conjugated semiconducting polymer under mechanical load. Journal of Applied Physics, 2020, 127, 045108.	2.5	8
22	Variableâ€Wavelength Quick Scanning Nanofocused Xâ€Ray Microscopy for In Situ Strain and Tilt Mapping. Small, 2020, 16, 1905990.	10.0	3
23	Multi-wavelength Bragg coherent X-ray diffraction imaging of Au particles. Journal of Applied Crystallography, 2020, 53, 170-177.	4.5	9
24	New insights into thermomechanical behavior of GeTe thin films during crystallization. Acta Materialia, 2020, 191, 60-69.	7.9	18
25	Plastic behaviour and deformation mechanisms in silicon nano-objects. Journal of Physics: Conference Series, 2019, 1190, 012004.	0.4	1
26	In situstructural evolution of single particle model catalysts under ambient pressure reaction conditions. Nanoscale, 2019, 11, 331-338.	5.6	10
27	In depth characterization of Ge-Si core-shell nanowires using X-ray coherent diffraction and time resolved pump-probe spectroscopy. Journal of Applied Physics, 2019, 126, 204304.	2.5	1
28	Towards a quantitative determination of strain in Bragg Coherent X-ray Diffraction Imaging: artefacts and sign convention in reconstructions. Scientific Reports, 2019, 9, 17357.	3.3	23
29	Controlling dislocation nucleation-mediated plasticity in nanostructures via surface modification. Acta Materialia, 2019, 166, 572-586.	7.9	40
30	Progress of in situ synchrotron X-ray diffraction studies on the mechanical behavior of materials at small scales. Progress in Materials Science, 2018, 94, 384-434.	32.8	50
31	Crystallographic orientation of facets and planar defects in functional nanostructures elucidated by nano-focused coherent diffractive X-ray imaging. Nanoscale, 2018, 10, 4833-4840.	5.6	14
32	Strain Distribution Induced in SOI Photonic Substrate by Through Silicon via Using Advanced Scanning X-Ray Nano-Diffraction. IEEE Transactions on Device and Materials Reliability, 2018, 18, 529-533.	2.0	2
33	In Situ Coherent X-ray Diffraction during Three-Point Bending of a Au Nanowire: Visualization and Quantification. Quantum Beam Science, 2018, 2, 24.	1.2	7
34	Three-point bending behavior of a Au nanowire studied by in-situ Laue micro-diffraction. Journal of Applied Physics, 2018, 124, .	2.5	5
35	In situ monitoring of stress change in GeTe thin films during thermal annealing and crystallization. Micro and Nano Engineering, 2018, 1, 63-67.	2.9	10
36	Low-temperature intrinsic plasticity in silicon at small scales. Acta Materialia, 2018, 161, 54-60.	7.9	25

#	Article	IF	Citations
37	Plasticity in inhomogeneously strained Au nanowires studied by Laue microdiffraction. MRS Advances, 2018, 3, 2331-2339.	0.9	0
38	In situ Bragg coherent X-ray diffraction during tensile testing of an individual Au nanowire. Journal of Applied Crystallography, 2018, 51, 781-788.	4.5	11
39	Evaluation of Alternative Atomistic Models for the Incipient Growth of ZnO by Atomic Layer Deposition. Journal of Electronic Materials, 2017, 46, 3512-3517.	2.2	6
40	A Complex Interrelationship between Temperature-Dependent Polyquaterthiophene (PQT) Structural and Electrical Properties. Journal of Physical Chemistry C, 2017, 121, 23149-23157.	3.1	2
41	Reactor for nano-focused x-ray diffraction and imaging under catalytic in situ conditions. Review of Scientific Instruments, 2017, 88, 093902.	1.3	7
42	3D Imaging of a Dislocation Loop at the Onset of Plasticity in an Indented Nanocrystal. Nano Letters, 2017, 17, 6696-6701.	9.1	37
43	Piezoelectric response and electrical properties of Pb(Zr1-xTix)O3 thin films: The role of imprint and composition. Journal of Applied Physics, 2017, 122, .	2.5	15
44	KB scanning of X-ray beam for Laue microdiffraction on accelero-phobic samples: application toin situmechanically loaded nanowires. Journal of Synchrotron Radiation, 2016, 23, 1395-1400.	2.4	10
45	Spatiotemporal Imaging of the Acoustic Field Emitted by a Single Copper Nanowire. Nano Letters, 2016, 16, 6592-6598.	9.1	29
46	An Atomistic View of the Incipient Growth of Zinc Oxide Nanolayers. Crystal Growth and Design, 2016, 16, 5339-5348.	3.0	14
47	X-ray nanodiffraction in forward scattering and Bragg geometry of a single isolated Agâ€“Au nanowire. Thin Solid Films, 2016, 617, 9-13.	1.8	0
48	Stress buildup during crystallization of thin chalcogenide films for memory applications: In situ combination of synchrotron X-Ray diffraction and wafer curvature measurements. Thin Solid Films, 2016, 617, 44-47.	1.8	8
49	Evolution of Crystal Structure During the Initial Stages of ZnO Atomic Layer Deposition. Chemistry of Materials, 2016, 28, 592-600.	6.7	31
50	In situ X-ray diffraction studies on the piezoelectric response of PZT thin films. Thin Solid Films, 2016, 603, 29-33.	1.8	13
51	Temperature dependency of the strain distribution induced by TSVs in silicon: A comparative study between micro-Laue and monochromatic nano-diffraction. Microelectronic Engineering, 2016, 156, 59-64.	2.4	1
52	Continuous and Collective Grain Rotation in Nanoscale Thin Films during Silicidation. Physical Review Letters, 2015, 115, 266101.	7.8	8
53	In situbending of an Au nanowire monitored by micro Laue diffraction. Journal of Applied Crystallography, 2015, 48, 291-296.	4.5	34
54	Strain and tilt mapping in silicon around copper filled TSVs using advanced X-ray nano-diffraction. Microelectronic Engineering, 2015, 137, 117-123.	2.4	13

#	Article	IF	Citations
55	Thermo-mechanical characterization of passive stress sensors in Si interposer. Microelectronics Reliability, 2015, 55, 738-746.	1.7	2
56	Through-silicon via-induced strain distribution in silicon interposer. Applied Physics Letters, 2015, 106, .	3.3	13
57	Inversion Domain Boundaries in GaN Wires Revealed by Coherent Bragg Imaging. ACS Nano, 2015, 9, 9210-9216.	14.6	62
58	In situ coupling of atomic force microscopy and sub-micrometer focused X-ray techniques. Materials Research Society Symposia Proceedings, 2014, 1712, 63.	0.1	1
59	Scanning force microscope forin situnanofocused X-ray diffraction studies. Journal of Synchrotron Radiation, 2014, 21, 1128-1133.	2.4	33
60	First stage of CoSi2 formation during a solid-state reaction. Journal of Applied Physics, 2014, 116, 245301.	2.5	6
61	Direct Observation of Gigahertz Coherent Guided Acoustic Phonons in Free-Standing Single Copper Nanowires. Journal of Physical Chemistry Letters, 2014, 5, 4100-4104.	4.6	32
62	Retrieval of the atomic displacements in the crystal from the coherent X-ray diffraction pattern. Journal of Synchrotron Radiation, 2014, 21, 774-783.	2.4	22
63	New insights into single-grain mechanical behavior from temperature-dependent 3-D coherent X-ray diffraction. Acta Materialia, 2014, 78, 46-55.	7.9	15
64	Silicide formation during reaction between Ni ultra-thin films and Si(001) substrates. Materials Letters, 2014, 116, 139-142.	2.6	11
65	Fast pole figure acquisition using area detectors at the DiffAbs beamline â€“ Synchrotron SOLEIL. Erratum. Journal of Applied Crystallography, 2014, 47, 482-482.	4.5	7
66	Anomalous coherent diffraction of core-shell nano-objects: A methodology for determination of composition and strain fields. Physical Review B, 2013, 87, .	3.2	7
67	Exploring Pdâ€“Si(001) and Pdâ€“Si(111) thin-film reactions by simultaneous synchrotron X-ray diffraction and substrate curvature measurements. Thin Solid Films, 2013, 530, 100-104.	1.8	8
68	Combined coherent x-ray micro-diffraction and local mechanical loading on copper nanocrystals. Journal of Physics: Conference Series, 2013, 425, 132003.	0.4	4
69	In situ coherent X-ray diffraction of isolated coreâ€“shell nanowires. Thin Solid Films, 2013, 530, 113-119.	1.8	9
70	CoSi2 ultra-thin layer formation kinetics and texture from X-ray diffraction. Thin Solid Films, 2013, 541, 17-20.	1.8	1
71	Decreasing reaction rate at the end of silicidation: In-situ CoSi2 XRD study and modeling. Microelectronic Engineering, 2013, 106, 125-128.	2.4	2
72	Strain inhomogeneity in copper islands probed by coherent X-ray diffraction. Thin Solid Films, 2013, 530, 120-124.	1.8	13

#	Article	IF	Citations
73	Concentration and Strain Fields inside a Ag/Au Coreâ€“Shell Nanowire Studied by Coherent X-ray Diffraction. Nano Letters, 2013, 13, 1883-1889.	9.1	23
74	Fast pole figure acquisition using area detectors at the DiffAbs beamline â€“ Synchrotron SOLEIL. Journal of Applied Crystallography, 2013, 46, 1842-1853.	4.5	47
75	Comparative study of metallic silicideâ€“germanide orthorhombic MnP systems. Journal of Physics Condensed Matter, 2013, 25, 355403.	1.8	3
76	Vibrational response of free standing single copper nanowire through transient reflectivity microscopy. Journal of Applied Physics, 2013, 114, 193509.	2.5	28
77	Thermo-mechanical study of a 2.5D passive silicon interposer technology: Experimental, numerical and In-Situ stress sensors developments. , 2013, , .		5
78	In situthree-dimensional reciprocal-space mapping during mechanical deformation. Journal of Synchrotron Radiation, 2012, 19, 688-694.	2.4	27
79	Thermoelasticity and interdiffusion in CuNi multilayers. Physical Review B, 2012, 85, .	3.2	7
80	Expected and unexpected plastic behavior at the micron scale: An in situ Î¼Laue tensile study. Acta Materialia, 2012, 60, 1252-1258.	7.9	38
81	In situ combined synchrotron X-ray diffraction and wafer curvature measurements during formation of thin palladium silicide film on Si(001) and Si (111). Nuclear Instruments & Methods in Physics Research B, 2012, 284, 74-77.	1.4	5
82	Local strain induced in silicon by Si3N4 lines: Modeling and experimental investigation via X-ray diffraction. Nuclear Instruments & Methods in Physics Research B, 2012, 284, 23-28.	1.4	3
83	First-principles study of nickel-silicides ordered phases. Journal of Alloys and Compounds, 2011, 509, 2639-2644.	5.5	52
84	Nanometer Scale Assessment of Mechanical Strain Induced in Silicon by a Periodic Line Array. Journal of Nanoscience and Nanotechnology, 2011, 11, 9160-9166.	0.9	1
85	Dislocation storage in single slip-oriented Cu micro-tensile samples: new insights via X-ray microdiffraction. Philosophical Magazine, 2011, 91, 1256-1264.	1.6	43
86	3D strain imaging in sub-micrometer crystals using cross-reciprocal space measurements: Numerical feasibility and experimental methodology. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 388-393.	1.4	6
87	Post Si(C)N hillock nucleation and growth in IC copper lines controlled by diffusional creep. Microelectronic Engineering, 2010, 87, 361-364.	2.4	7
88	X-ray microbeam strain investigation on Cuâ€“MEMS structures. Microelectronic Engineering, 2010, 87, 394-397.	2.4	8
89	Nickel silicide encroachment formation and characterization. Microelectronic Engineering, 2010, 87, 245-248.	2.4	32
90	Out-of-plane stresses arising from grain interactions in textured thin films. Acta Materialia, 2010, 58, 2452-2463.	7.9	16

#	Article	IF	Citations
91	Finite element simulations of coherent diffraction in elastoplastic polycrystalline aggregates. Comptes Rendus Physique, 2010, 11, 293-303.	0.9	4
92	Lattice instabilities in hexagonal NiSi: A NiAs prototype structure. Physical Review B, 2010, 81, .	3.2	4
93	Methodology for studying strain inhomogeneities in polycrystalline thin films duringin situthermal loading using coherent x-ray diffraction. New Journal of Physics, 2010, 12, 035018.	2.9	24
94	Relation between strain and composition in coherent epitaxial Cu/Ni multilayers: Influence of strong concentration gradients. Physical Review B, 2009, 79, .	3.2	4
95	High-resolution X-ray diffraction as a tool to investigate the evolution of local stress in sub-micrometric Si lines isolated by periodic arrays of oxide-filled trenches. Materials Science in Semiconductor Processing, 2009, 12, 64-70.	4.0	1
96	First-principles study of the structural, electronic, vibrational, and elastic properties of orthorhombic NiSi. Physical Review B, 2009, 79, .	3.2	202
97	Self-aligned nickelâ€“platinum silicide oxidation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 155-158.	3.5	5
98	Texture and strain in narrow copper damascene interconnect lines: An X-ray diffraction analysis. Microelectronic Engineering, 2008, 85, 2175-2178.	2.4	5
99	Local strains induced in silicon channel by a periodic array of nitride capped poly lines investigated by high resolution X-ray diffraction. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 129-132.	3.5	2
100	Influence of crystallographic orientation on local strains in silicon: A combined high-resolution X-ray diffraction and finite element modelling investigation. Thin Solid Films, 2008, 516, 8042-8048.	1.8	9
101	Nitrogen impurity effects on nickel silicide formation at low temperatures â€“ New â€œnitrogen co-plasmaâ€•approach. Microelectronic Engineering, 2008, 85, 2005-2008.	2.4	7
102	Diffraction analysis of elastic strains in micro and nanostructures. Zeitschrift FÃ¼r Kristallographie, 2008, 223, 569-574.	1.1	4
103	Applicability of an iterative inversion algorithm to the diffraction patterns from inhomogeneously strained crystals. Physical Review B, 2008, 78, .	3.2	35
104	Strain field in silicon on insulator lines using high resolution x-ray diffraction. Applied Physics Letters, 2007, 90, 111914.	3.3	40
105	Inversion of the diffraction pattern from an inhomogeneously strained crystal using an iterative algorithm. Physical Review B, 2007, 76, .	3.2	70
106	Investigating Interdiffusion in Mo/V Multilayers from X-Ray Scattering and Kinetic Simulations. Defect and Diffusion Forum, 2007, 264, 13-18.	0.4	1
107	Local strain in a 3D nano-crystal revealed by 2D coherent X-ray diffraction imaging. Thin Solid Films, 2007, 515, 5557-5562.	1.8	9
108	Impact of surface preparation on nickelâ€“platinum alloy silicide phase formation. Microelectronic Engineering, 2007, 84, 2523-2527.	2.4	14

#	Article	IF	Citations
109	Investigation by High Resolution X-ray Diffraction of the local strains induced in Si by periodic arrays of oxide filled trenches. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 2542-2547.	1.8	13
110	Residual stress analysis in micro- and nano-structured materials by X-ray diffraction. International Journal of Materials and Product Technology, 2006, 26, 354.	0.2	8
111	Numerical modeling of stress build up during nickel silicidation under anisothermal annealing. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 135, 95-102.	3.5	6
112	X-ray scattering: A powerful probe of lattice strain in materials with small dimensions. Applied Surface Science, 2006, 253, 182-187.	6.1	7
113	Stresses in Copper Damascene Lines: In-situ Measurements and Finite Element Analysis. AIP Conference Proceedings, 2006, , .	0.4	7
114	Diffraction from Periodic Arrays of Oxide-Filled Trenches in Silicon: Investigation of Local Strains. Materials Research Society Symposia Proceedings, 2006, 913, 1.	0.1	5
115	Mechanical characterization of low-k and barrier dielectric thin films. Microelectronic Engineering, 2005, 82, 368-373.	2.4	27
116	Pipe-diffusion ripening of Si precipitates in Al-0.5%Cu-1%Si thin films. Philosophical Magazine, 2005, 85, 3541-3552.	1.6	8
117	Stress Development and Relaxation during Reaction of a Cobalt Film with a Silicon Substrate. Defect and Diffusion Forum, 2005, 237-240, 518-523.	0.4	3
118	Investigation of local stress fields: Finite element modelling and High Resolution X-Ray Diffraction. Materials Research Society Symposia Proceedings, 2005, 875, 1.	0.1	9
119	Combined synchrotron x-ray diffraction and wafer curvature measurements during Niâ€“Si reactive film formation. Applied Physics Letters, 2005, 87, 041904.	3.3	40
120	Stress Development during the Reactive Formation of Silicide Films. Defect and Diffusion Forum, 2005, 237-240, 801-812.	0.4	8
121	Simulation et dÃ©termination par rayons X des contraintes dans des micro-composants modÃ¨les. European Physical Journal Special Topics, 2004, 118, 109-115.	0.2	0
122	X-ray scattering: a wonderful tool to probe lattice strains in materials with small dimensions. Materials Research Society Symposia Proceedings, 2004, 840, Q3.2.1.	0.1	0
123	Stresses and interfacial structure in Auâ€“Ni and Agâ€“Cu metallic multilayers. Scripta Materialia, 2004, 50, 717-721.	5.2	15
124	Exploring Niâ€“Si thin-film reactions by means of simultaneous synchrotron X-Ray diffraction and substrate curvature measurements. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 67-71.	3.5	12
125	In situ study of stress evolution during the reaction of a nickel film with a silicon substrate. Microelectronic Engineering, 2004, 76, 318-323.	2.4	22
126	In situstress measurements during the growth at different temperatures of Agâ€“Cu(111) multilayers. Journal of Applied Physics, 2004, 95, 1152-1161.	2.5	4

#	Article	IF	Citations
127	Stresses and Interfacial Structure in Metal Films and Multilayers of Nanometre Thickness. Journal of Metastable and Nanocrystalline Materials, 2004, 19, 129-152.	0.1	3
128	Impact of thermal cycling on the evolution of grain, precipitate and dislocation structure in Al, 0.5% Cu, 1% Si thin films. Microelectronic Engineering, 2003, 70, 447-454.	2.4	10
129	Simulation of local mechanical stresses in lines on substrate. Microelectronic Engineering, 2003, 70, 455-460.	2.4	8
130	First stages of silicidation in Ti/Si thin films. Microelectronic Engineering, 2003, 70, 166-173.	2.4	4
131	In-situ study of stress evolution during solid state reaction of Pd with Si(001) using synchrotron radiation. Microelectronic Engineering, 2003, 70, 436-441.	2.4	6
132	X-ray diffraction from inhomogeneous thin films of nanometre thickness: modelling and experiment. Journal of Applied Crystallography, 2003, 36, 154-157.	4.5	9
133	Stresses arising from a solid state reaction between palladium films and Si(001) investigated byin situcombined x-ray diffraction and curvature measurements. Journal of Applied Physics, 2003, 94, 1584-1591.	2.5	32
134	Influence of Si substrate orientation on stress development in Pd silicide films grown by solid-state reaction. Applied Physics Letters, 2003, 83, 1334-1336.	3.3	20
135	The early stages of stress development during epitaxial growth of Ag/Cu multilayers. Materials Research Society Symposia Proceedings, 2003, 791, 1.	0.1	0
136	Thermal expansion and stress development in the first stages of silicidation in Ti/Si thin films. Journal of Applied Physics, 2003, 94, 7083-7090.	2.5	8
137	Interplay between Anisotropic Strain Relaxation and Uniaxial Interface Magnetic Anisotropy in Epitaxial Fe Films on (001) GaAs. Physical Review Letters, 2003, 90, 017205.	7.8	128
138	Cubic local order around Al and intermixing in short-period AlN/TiN multilayers studied by Al K-edge extended x-ray absorption fine structure spectroscopy and x-ray diffraction. Applied Physics Letters, 2003, 82, 3659-3661.	3.3	13
139	Influence of segregation on the measurement of stress in thin films. Journal of Applied Physics, 2002, 91, 2951-2958.	2.5	9
140	Stresses in Multilayer Systems: Test of the sin2Î· Method. Advanced Engineering Materials, 2002, 4, 557-561.	3.5	1
141	Chemically diffuse interface in (1 1 1) Auâ€“Ni multilayers: an anomalous X-ray diffraction analysis. Applied Surface Science, 2002, 188, 110-114.	6.1	5
142	Microstructural analysis of AU/NI multilayers interfaces by SAXS and STM. Applied Surface Science, 2002, 188, 182-187.	6.1	12
143	In situ study of strain evolution during thin film Ti/Al(Si,Cu) reaction using synchrotron radiation. Microelectronic Engineering, 2002, 64, 81-89.	2.4	2
144	Stress evolution in a Ti/Al(Si,Cu) dual layer during annealing. Materials Research Society Symposia Proceedings, 2001, 673, 1.	0.1	1

#	Article	IF	Citations
145	X-Ray Diffraction Analysis and Modeling of Strain Induced Thermal Cycling in a Thin Aluminum (011) Bicrystal Film. Materials Research Society Symposia Proceedings, 2001, 695, 1.	0.1	3
146	Interfacial structure in (111) Au:Ni multilayers investigated by anomalous x-ray diffraction. Physical Review B, 2001, 64, .	3.2	33
147	In Situ Stress and Strain Measurements During the Growth of Cu/Ni (001) Multilayers. Materials Research Society Symposia Proceedings, 2000, 615, 861.	0.1	1
148	In Situ Curvature and Diffraction Studies of Pd Films on Si(001) During Solid-State Reaction. Materials Research Society Symposia Proceedings, 2000, 615, 831.	0.1	0
149	Chemical vapor deposition of siliconâ€“germanium heterostructures. Journal of Crystal Growth, 2000, 216, 171-184.	1.5	32
150	Stress, porosity measurements and corrosion behaviour of AlN films deposited on steel substrates. Thin Solid Films, 2000, 359, 221-227.	1.8	34
151	Raman spectra of TiN/AlN superlattices. Thin Solid Films, 2000, 380, 252-255.	1.8	43
152	Interdependence of elastic strain and segregation in metallic multilayers: An x-ray diffraction study of (111) Au/Ni multilayers. Journal of Applied Physics, 2000, 87, 1172-1181.	2.5	50
153	Asymptotic behaviour of stress establishment in thin films. Surface Science, 2000, 465, L764-L770.	1.9	30
154	Segregation and strain relaxation in Au/Ni multilayers: An in situ experiment. Applied Physics Letters, 1999, 75, 914-916.	3.3	27
155	Interdependence between strain relaxation and segregation in Au/Ni multilayers. Journal of Magnetism and Magnetic Materials, 1999, 198-199, 593-595.	2.3	0
156	Internal Stress In Sputtered Silver Nickel Thin Films And Multilayers: Sputtering Pressure And Thickness Effects. Materials Research Society Symposia Proceedings, 1999, 562, 123.	0.1	1
157	An In-Situ Study of the Segregation and the Strain Relaxation During Growth of Gold and Nickel Ultrathin Films. Materials Research Society Symposia Proceedings, 1999, 562, 189.	0.1	0
158	Limits of validity of the crystallite group method in stress determination of thin film structures. Thin Solid Films, 1998, 319, 9-15.	1.8	42
159	Structure characterization of metallic multilayers by symmetric and asymmetric X-ray diffraction. Thin Solid Films, 1998, 319, 78-80.	1.8	8
160	Correlation between the microwave surface resistance and the volumic fraction of a-axis grains in YBa2Cu3O7â˜'x films. Physica C: Superconductivity and Its Applications, 1998, 308, 16-20.	1.2	7
161	Effect of Co, Pt, and Au additions on the stability and epitaxy of NiSi2 films on (111)Si. Journal of Applied Physics, 1998, 84, 2583-2590.	2.5	66
162	Stress in Ag/Ni Multilayers: A Comparison of Specimen-Curvature and X-Ray Diffraction Methods. Materials Research Society Symposia Proceedings, 1997, 472, 299.	0.1	4

#	Article	IF	Citations
163	Residual Stresses in Ultrathin Metal Sublayers Within Au/Ni Multilayers. Materials Research Society Symposia Proceedings, 1997, 475, 363.	0.1	4
164	YBCO films deposited on YAlO/sub 3/ substrates: microstructure and transport properties. IEEE Transactions on Applied Superconductivity, 1997, 7, 1268-1271.	1.7	3
165	Twinning behaviour in YBCO and PBCO thin films and in PBCO-YBCO superlattices. Journal of Alloys and Compounds, 1997, 251, 322-327.	5.5	6
166	Structural and magnetic properties of Ni/Cr multilayers. Journal of Magnetism and Magnetic Materials, 1997, 165, 205-207.	2.3	3
167	Comparison between different X-ray diffraction methods to extract strains in metallic multilayers. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1997, 19, 577-583.	0.4	2
168	The composition analysis of YBa 2 Cu 3 O 7-Î´ or PrBa 2 Cu 3 O 7-Î´ thin films and (YBa 2 Cu 3 O 7-Î´ /PrBa 2 Cu) Tj ETQq0 0 0 rgBT /Overlo 1061-1065.	1.5	2
169	Stresses during Silicide Formation: A Review. Defect and Diffusion Forum, 1996, 129-130, 137-150.	0.4	30
170	Twinning orientation in YBa2Cu3O7â˜'x films deposited on YAlO3 substrates. Applied Physics Letters, 1996, 69, 1942-1944.	3.3	11
171	Influence of the microstructure on the residual strains in (111) Au/Ni multilayers. Journal of Magnetism and Magnetic Materials, 1996, 156, 31-32.	2.3	1
172	Microstructure and residual stresses in (111) multilayers. Thin Solid Films, 1996, 275, 29-34.	1.8	6
173	Field modulated microwave absorption in YBa2Cu3O7/PrBa2Cu3O7 multilayers. Journal of Low Temperature Physics, 1996, 105, 1061-1066.	1.4	1
174	Formation of Ni silicide from Ni(Au) films on (111)Si. Journal of Applied Physics, 1996, 79, 4078.	2.5	46
175	Mechanical and Microstructural Studies of (111) Au/Ni Multilayers. European Physical Journal Special Topics, 1996, 06, C7-135-C7-142.	0.2	1
176	Transport and Low Temperature Specific Heat Measurements of CrSi2 Single Crystals. Materials Research Society Symposia Proceedings, 1995, 402, 343.	0.1	4
177	Angular dependence of the magnetoresistance of TiSi2 single crystals. Applied Surface Science, 1995, 91, 98-102.	6.1	1
178	High Quality YBa₂Cu₃O_{7-x} Superconducting Thin Films Grown by MOCVD. European Physical Journal Special Topics, 1995, 05, C5-365-C5-371.	0.2	5
179	Microwave properties of YBCO thin films. IEEE Transactions on Applied Superconductivity, 1995, 5, 1737-1740.	1.7	22
180	Growth of (YBaCuO)_m/(PrBaCuO)_n Superlattices by MOCVD. European Physical Journal Special Topics, 1995, 05, C5-423-C5-430.	0.2	2

#	Article	IF	Citations
181	Measurements of critical currents as a function of temperature in YBa2Cu3O7-xthin films: a comparative study. Superconductor Science and Technology, 1994, 7, 195-205.	3.5	7
182	Thermal modelization and experiments on the current of superconducting microbridges dependence to light in the 10â€“90K range. Physica B: Condensed Matter, 1994, 194-196, 2125-2126.	2.7	1
183	Irreversibility line of YBa2Cu3O7 thin films studied by field modulated microwave absorption. Physica C: Superconductivity and Its Applications, 1994, 235-240, 3153-3154.	1.2	3
184	Texture influence on critical current density of YBCO films deposited on (100)-MgO substrates. Physica C: Superconductivity and Its Applications, 1994, 235-240, 627-628.	1.2	12
185	Transmission electron microscopy studies of thin films of YBa2Cu3O7-x. Physica C: Superconductivity and Its Applications, 1994, 235-240, 655-656.	1.2	1
186	Growth of YBa2Cu3O7â^'x / PrBa2Cu3O7â^'x heterostructures by chemical vapor deposition. Physica C: Superconductivity and Its Applications, 1994, 235-240, 723-724.	1.2	2
187	Diffusion of elements implanted in amorphous titanium disilicide. Applied Surface Science, 1993, 73, 167-174.	6.1	3
188	Low temperature specific heat measurements of VSi2, NbSi2 and TaSi2. Applied Surface Science, 1993, 73, 232-236.	6.1	4
189	Low temperature specific heat of VSi2, NbSi2, and TaSi2. Journal of Low Temperature Physics, 1993, 92, 335-351.	1.4	35
190	Fundamental and harmonic a.c. susceptibility response of MOCVD YBa2Cu3O7 thin films: Model of flux line behaviour. Cryogenics, 1993, 33, 497-501.	1.7	1
191	Transport critical current in MOCVD YBa2Cu3O7 thin films using a pulse technique. Journal of Alloys and Compounds, 1993, 195, 475-478.	5.5	4
192	Comparative study of the irreversibility line and of harmonic generation in field modulated microwave absorption on YBa2Cu3O7 thin films. Journal of Alloys and Compounds, 1993, 195, 587-590.	5.5	3
193	Electrical and optical properties of silicide single crystals and thin films. Materials Science and Engineering Reports, 1993, 9, 141-200.	5.8	94
194	Growth and properties of MOCVD YBa2Cu3O7â^'x thin films. Journal of Alloys and Compounds, 1993, 195, 287-290.	5.5	10
195	Preparation of YBa2Cu3O7â^'xfilms and YBa2Cu3O7â^'x/Y2O3multilayers using coevaporation and atomic oxygen. Journal of Applied Physics, 1993, 73, 3096-3098.	2.5	11
196	Thinâ€film growth and compositional effects in YBa2Cu3O7â^'xlayers prepared by metalorganic chemical vapor deposition. Journal of Applied Physics, 1993, 74, 4631-4642.	2.5	35
197	Precursor Delivery for the Deposition of Superconducting Oxides: a Comparison Between Solid Sources and Aerosol. Materials Research Society Symposia Proceedings, 1993, 335, 209.	0.1	1
198	Dopant diffusion in silicides: Effect of diffusion paths. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1992, 10, 907-911.	2.1	6

#	Article	IF	Citations
199	Superconductivity inTaSi2single crystals. Physical Review B, 1992, 45, 4803-4806.	3.2	27
200	In-Situ Preparation of Y-Ba-Cu-O Thin Films Using Mass-Spectrometer Rate Control and Atomic Oxygen. Materials Research Society Symposia Proceedings, 1992, 275, 299.	0.1	2
201	Magnetic properties of superconducting YBa2Cu3O7-x CVD thin films. , 1992, , 79-84.		0
202	Structure and morphology of YBa2Cu3O7â^'x LPCVD layers. Physica C: Superconductivity and Its Applications, 1991, 180, 42-45.	1.2	6
203	Superconducting properties of YBa2Cu3O7â^'x films deposited by chemical vapor deposition. Physica C: Superconductivity and Its Applications, 1991, 185-189, 2113-2114.	1.2	2
204	The reaction of scandium thin films with silicon: diffusion, nucleation, resistivities. Applied Surface Science, 1991, 53, 138-146.	6.1	15
205	Diffusion of dopants in tungsten disilicide: effects of diffusion paths. Applied Surface Science, 1991, 53, 165-170.	6.1	5
206	Low temperature specific heat of CoSi2. Applied Surface Science, 1991, 53, 240-242.	6.1	3
207	Some transport properties of single crystals of group Va transition metal disilicides. Applied Surface Science, 1991, 53, 247-253.	6.1	26
208	Resistivity and magnetoresistance of monocrystalline TaSi2 and VSi2. Surface and Coatings Technology, 1991, 45, 237-243.	4.8	12
209	Some titanium germanium and silicon compounds: Reaction and properties. Journal of Materials Research, 1990, 5, 1453-1462.	2.6	66
210	Oxidation and formation mechanisms in disilicides: VSi2and CrSi2, inert marker experiments and interpretation. Journal of Applied Physics, 1990, 68, 6213-6223.	2.5	8
211	Oxidation of titanium, manganese, iron, and niobium silicides: Marker experiments. Journal of Applied Physics, 1990, 68, 5133-5139.	2.5	24
212	Respective mobilities of metal and silicon in disilicides: Bilayers of chromium with molybdenum or tungsten. Journal of Applied Physics, 1990, 67, 2410-2414.	2.5	11
213	A.c. characterization of pyrosol and C.V.D. made high Tc materials. Journal of the Less Common Metals, 1990, 164-165, 1393-1399.	0.8	9
214	Organometallic chemical vapor deposition of superconducting YBa2Cu3O7 â^' Î´ films. Journal of the Less Common Metals, 1990, 164-165, 444-450.	0.8	19
215	Mechanisms for success or failure of diffusion barriers between aluminum and silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1989, 7, 875-880.	2.1	36
216	Reaction of titanium with germanium and siliconâ€germanium alloys. Applied Physics Letters, 1989, 54, 228-230.	3.3	68

#	Article	IF	Citations
217	Analysis of the electrical resistivity of Ti, Mo, Ta, and W monocrystalline disilicides. Journal of Applied Physics, 1989, 65, 1584-1590.	2.5	43
218	Ion-implantation-induced fluorine agglomeration in tungsten disilicide prepared by low-pressure chemical vapour deposition. Nuclear Instruments & Methods in Physics Research B, 1989, 40-41, 595-598.	1.4	1
219	Nucleation and growth in the reaction of titanium with germanium and some silicon-germanium alloys. Applied Surface Science, 1989, 38, 27-36.	6.1	41
220	Some properties of CrxV1â^'xSi2 and CrxMo1â^'xSi2 thin films. Applied Surface Science, 1989, 38, 94-105.	6.1	4
221	Metallurgical reinvestigation of rare earth silicides. Applied Surface Science, 1989, 38, 156-161.	6.1	53
222	The high residual resistivity of CoSi2: Evidence for a homogeneity range. Applied Surface Science, 1989, 38, 88-93.	6.1	8
223	Bilayers with chromium disilicide: Chromium-vanadium. Applied Surface Science, 1989, 38, 106-116.	6.1	7
224	Comparison of the diffusion barrier properties of tungsten films prepared by hydrogen and silicon reduction of tungsten hexafluoride. Thin Solid Films, 1989, 171, 343-357.	1.8	13
225	Magnetic and transmission electron microscopy studies of the formation of cobalt silicide thin films. Journal of Applied Physics, 1988, 64, 3014-3017.	2.5	7
226	The diffusion of elements implanted in films of cobalt disilicide. Journal of Applied Physics, 1988, 64, 2973-2980.	2.5	61
227	Tungstenâ€“rhenium alloys as diffusion barriers between aluminum and silicon. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 1650-1655.	2.1	14
228	Diffusion of Sb, Ga, Ge, and (As) in TiSi2. Journal of Applied Physics, 1988, 63, 5335-5345.	2.5	49
229	Diffusion of boron, phosphorus, and arsenic implanted in thin films of cobalt disilicide. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 1736-1739.	2.1	19
230	Low-temperature specific heat ofMoSi2. Physical Review B, 1988, 37, 10364-10366.	3.2	11
231	Reacted amorphous layers: Tantalum and niobium oxides. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1988, 58, 529-538.	0.6	14
232	de Haasâ€“van Alphen effect inMoSi2. Physical Review B, 1987, 35, 7936-7938.	3.2	18
233	Multispectral Spectroscopic Ellipsometry-A New Tool for In Situ Surface Analysis. Materials Research Society Symposia Proceedings, 1987, 101, 403.	0.1	6
234	Crystal growth, characterization and resistivity measurements of TiSi2 single crystals. Journal of the Less Common Metals, 1987, 136, 175-182.	0.8	23

#	Article	IF	Citations
235	Experimental study of partial densities of states in MoSi2. Solid State Communications, 1987, 64, 129-132.	1.9	8
236	Optical properties of WSi2 and MoSi2 single crystals as measured by spectroscopic ellipsometry and reflectometry. Solid State Communications, 1987, 62, 455-459.	1.9	32
237	Electronic properties of CoSi2 studied by reflectivity and spectroscopic ellipsometry. Solid State Communications, 1986, 60, 923-926.	1.9	26
238	Resistivity and magnetoresistance of high-purity monocrystalline MoSi2. Journal of Physics F: Metal Physics, 1986, 16, 1745-1752.	1.6	28
239	Molybdenum disilicide: Crystal growth, thermal expansion and resistivity. Solid State Communications, 1985, 55, 629-632.	1.9	114
240	An inâ€situ synchrotron Xâ€ray diffraction study on the influence of hydrogen on the crystallization of Geâ€rich Ge 2 Sb 2 Te 5. Physica Status Solidi - Rapid Research Letters, 0, , .	2.4	2